

General Description:

The LW8810AT uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is SOT23-6L, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances
- ESD Rating: HBM $\geq 1000V$

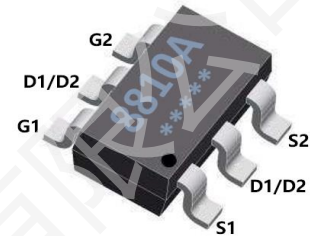
Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

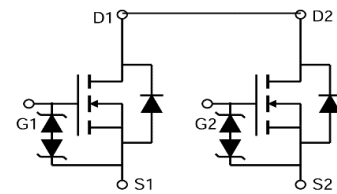


V_{DSS}	20	V
I_D	7.0	A
P_D	1.4	W
$R_{DS(ON)}$ TYPE	14	m Ω

Marking and Pin Assignment



Inner Equivalent Principium Chart



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
8810A/D.C.	LW8810AT	SOT23-6L	Reel	3000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		20	V
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$	7.0	A
	Continuous Drain Current	$T_A=100^\circ\text{C}$	4.4	A
I_{DM}^{a1}	Pulsed Drain Current		28	A
E_{AS}^{a2}	Single pulse avalanche energy		27	mJ
V_{GS}	Gate-to-Source Voltage		± 10	V
P_D	Power Dissipation		1.4	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering		260	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	89.3	$^\circ\text{C/W}$

Electrical Characteristic ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=20V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+10V, V_{DS}=0V$	--	--	5.0	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-10V, V_{DS}=0V$	--	--	-5.0	μA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=4.5V, I_D=7.0A$	--	14	18	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=2.5V, I_D=5.0A$	--	18	24	$m\Omega$
$R_{DS(ON)3}$	Drain-to-Source On-Resistance	$V_{GS}=1.8V, I_D=3.0A$	--	25.5	36	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$	--	714	--	pF
C_{oss}	Output Capacitance	$V_{DS}=10V$	--	127	--	
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	--	111	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	3.3	--	Ω

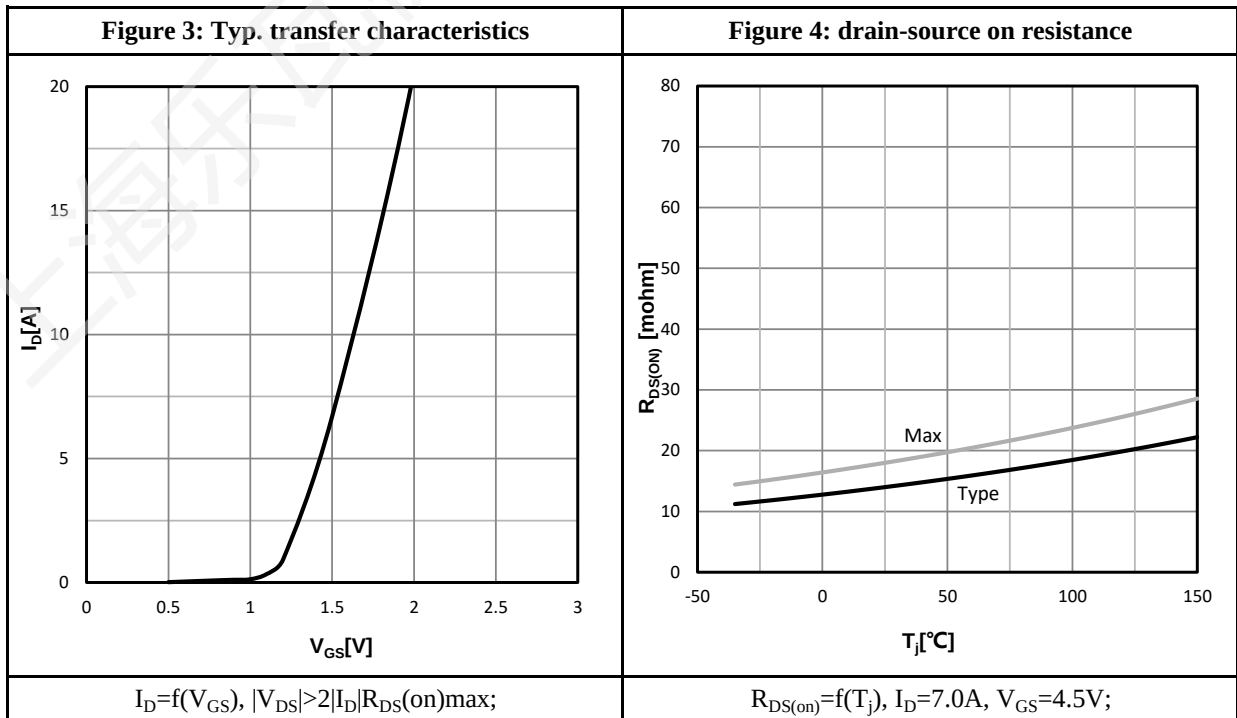
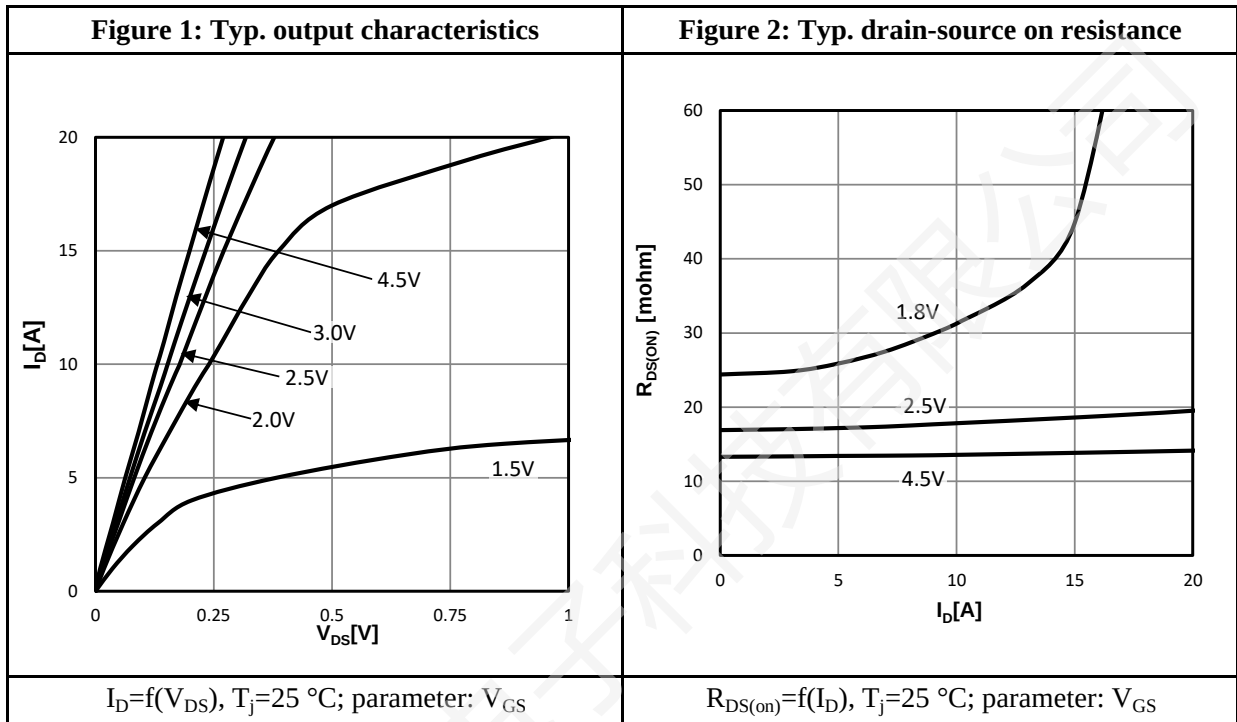
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=7.0A$	--	10	--	ns
t_r	Rise Time	$V_{DS}=10V$	--	11	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=4.5V$	--	35	--	
t_f	Fall Time	$R_G=3.0\Omega$	--	30	--	
Q_g	Total Gate Charge	$V_{GS}=4.5V$	--	8.9	--	nC
Q_{gs}	Gate to Source Charge	$V_{DS}=10V$	--	0.9	--	
Q_{gd}	Gate to Drain Charge	$I_D=7.0A$	--	2.7	--	

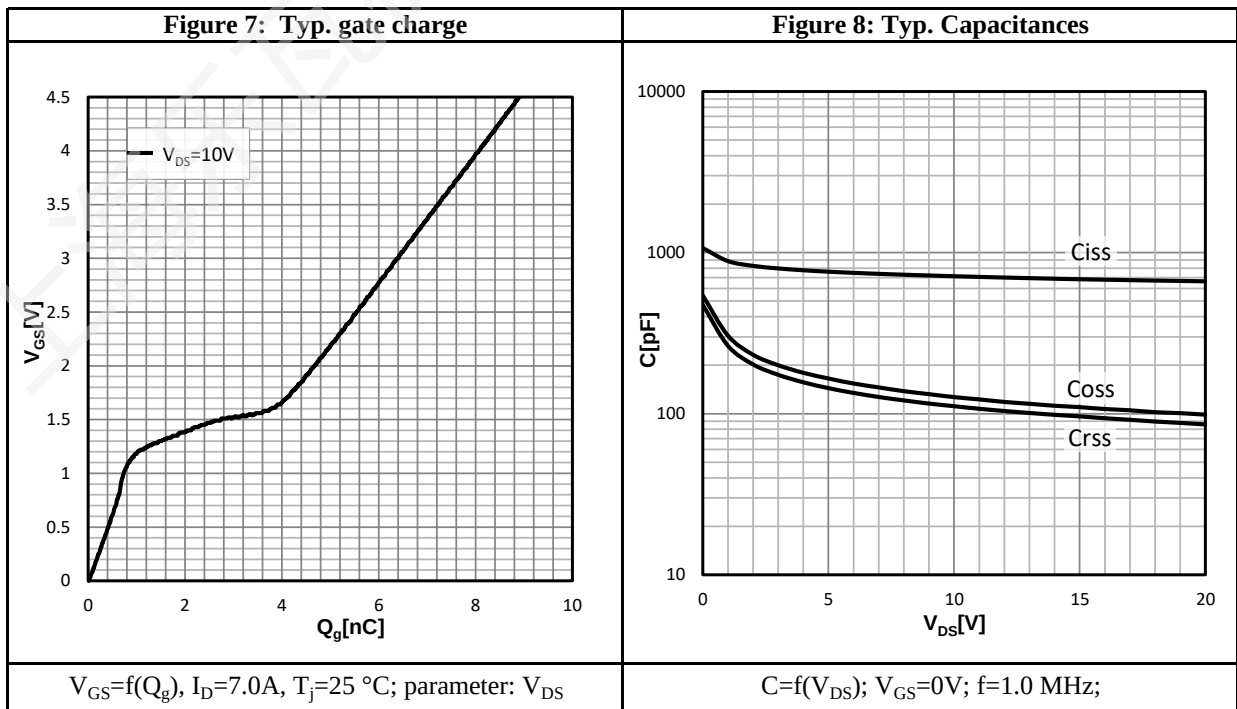
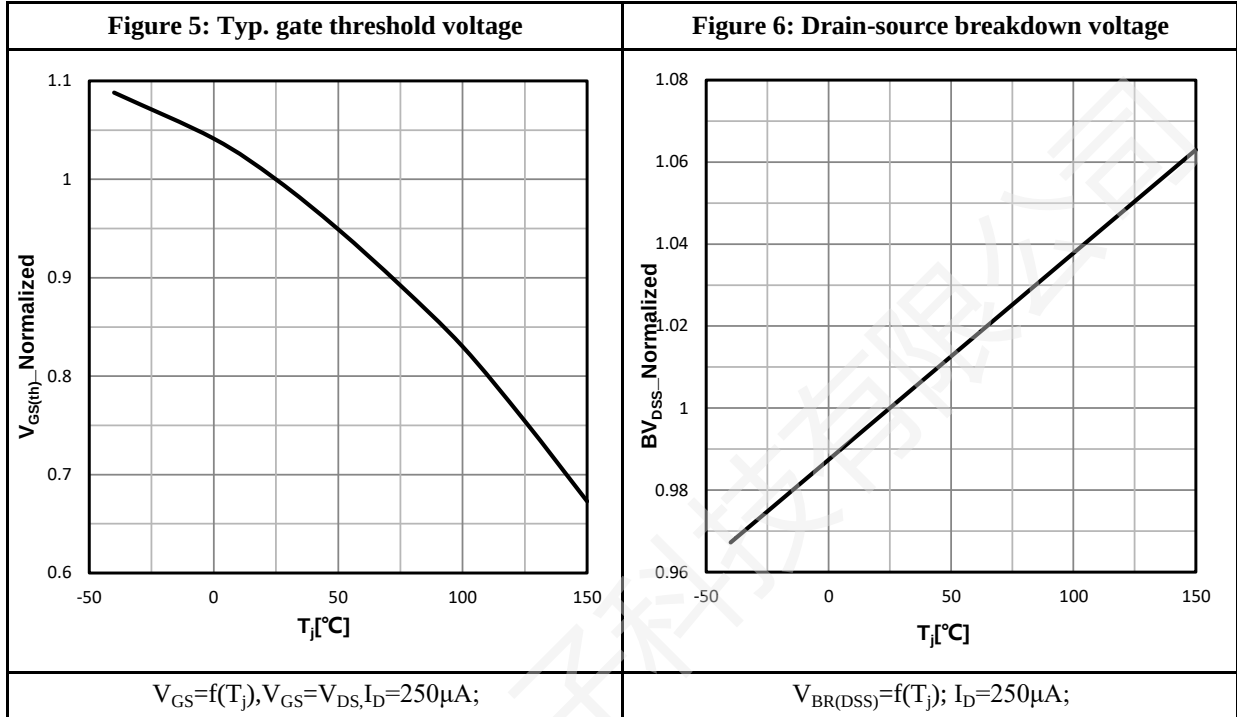
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_A=25\text{ }^{\circ}\text{C}$	--	--	7.0	A
V_{SD}	Diode Forward Voltage	$I_S=7.0A, V_{GS}=0V$	--	--	1.2	V

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: $V_{DD}=10V, L=0.1mH, R_G=25\Omega$, Starting $T_J=25\text{ }^{\circ}\text{C}$

a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

Characteristics Curve:




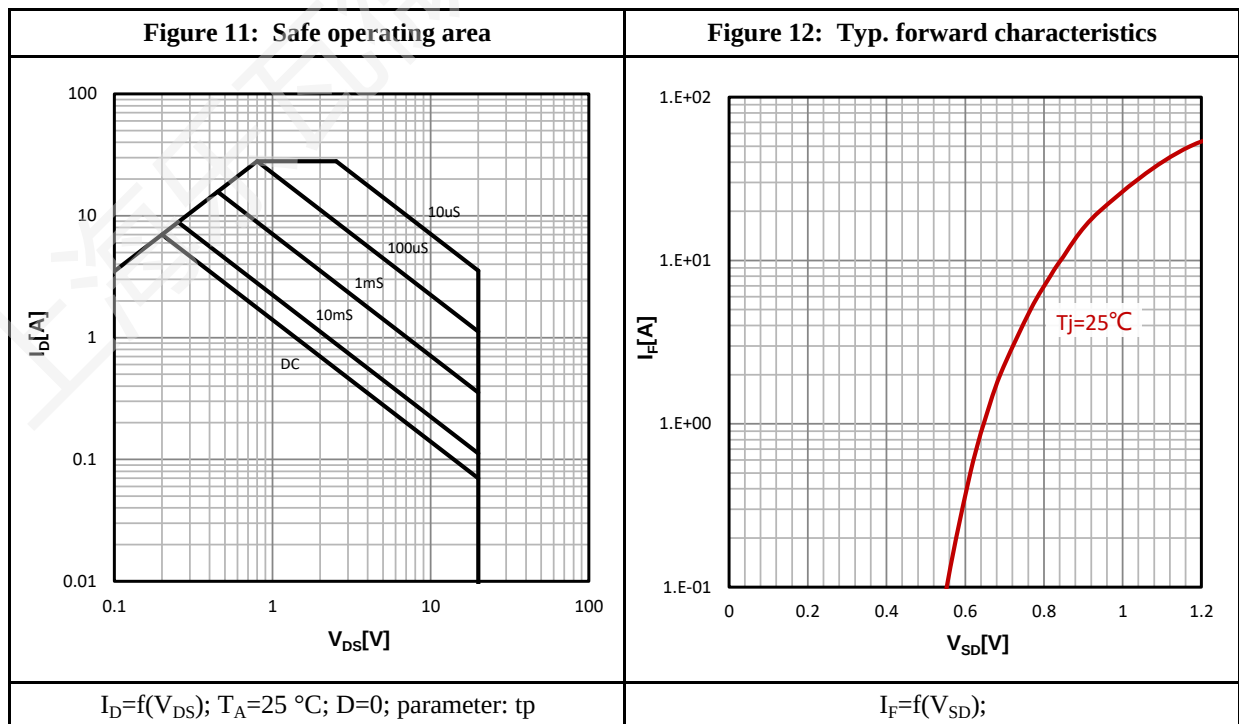
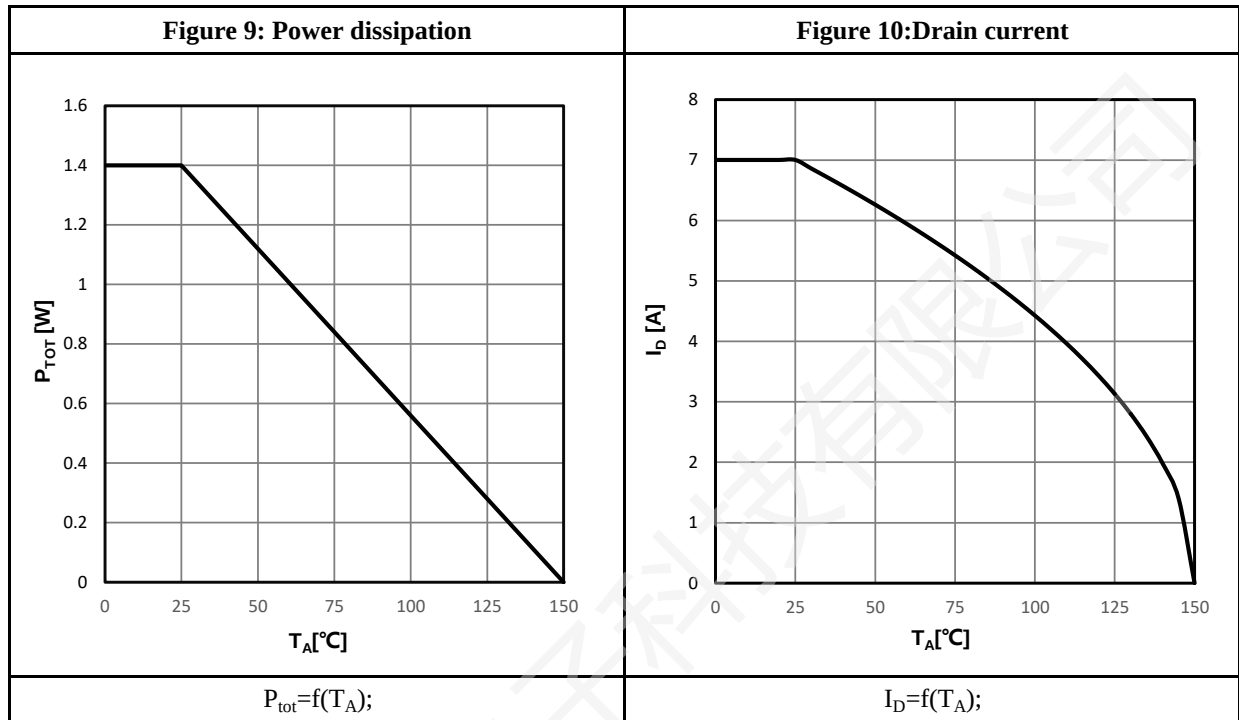
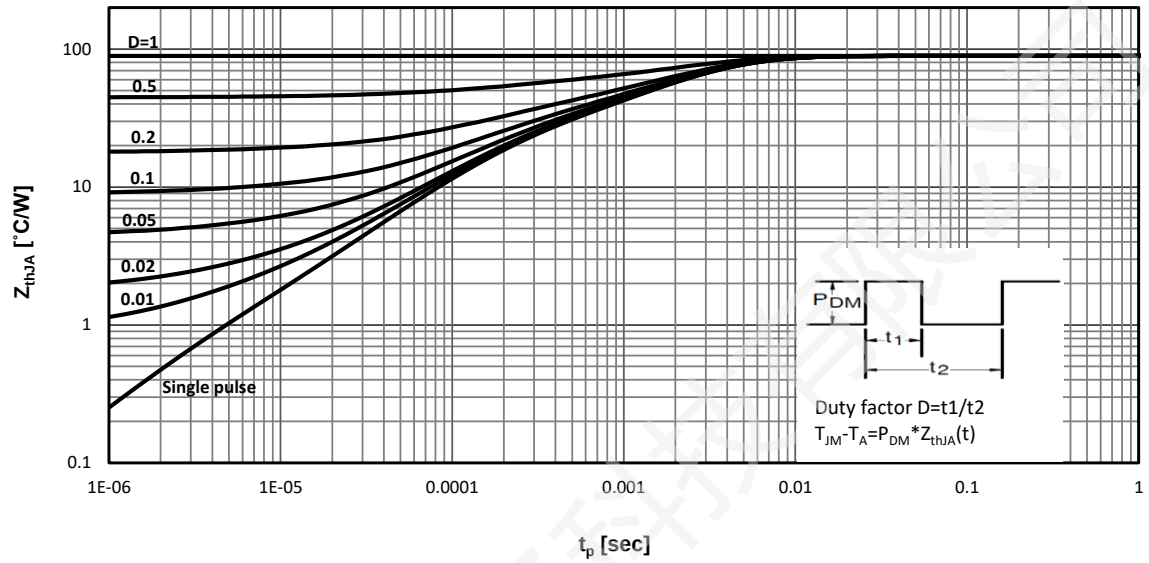
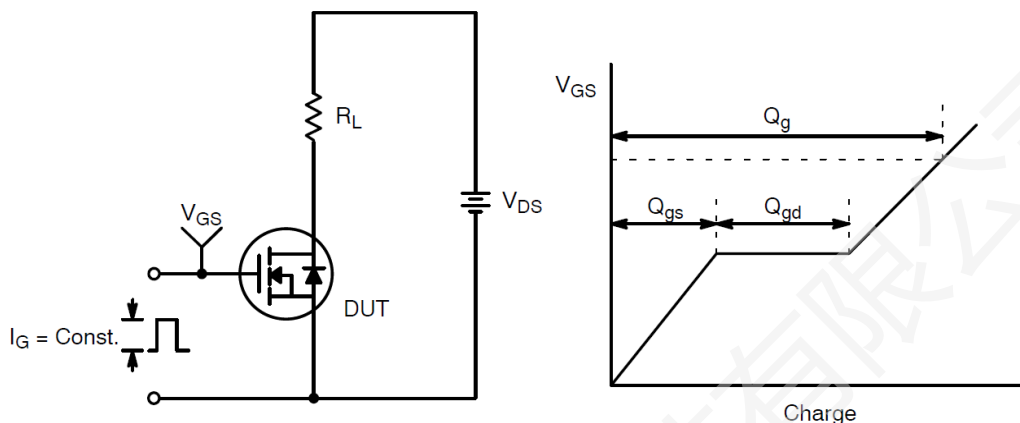
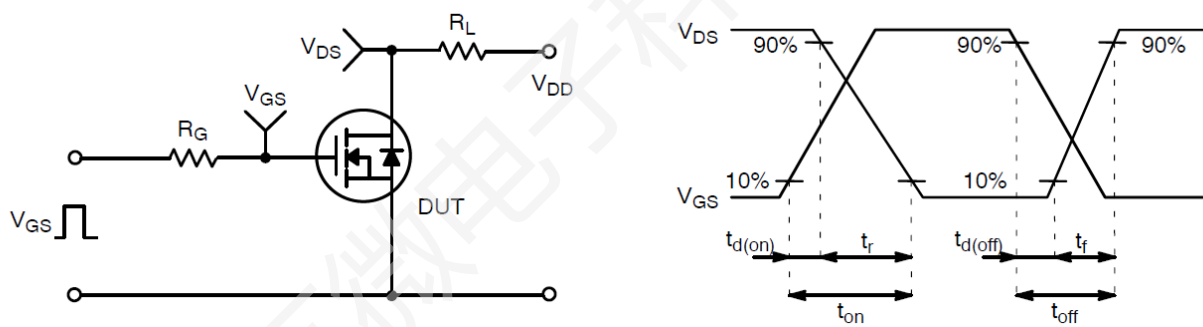
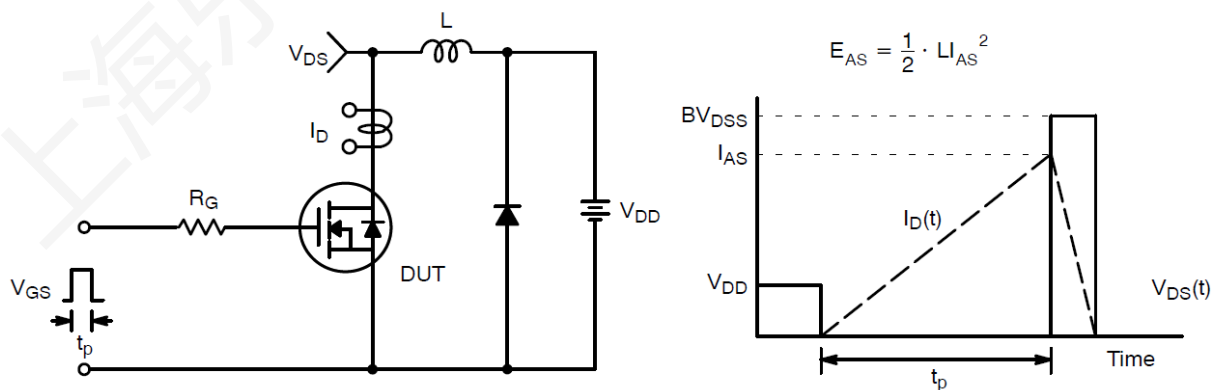
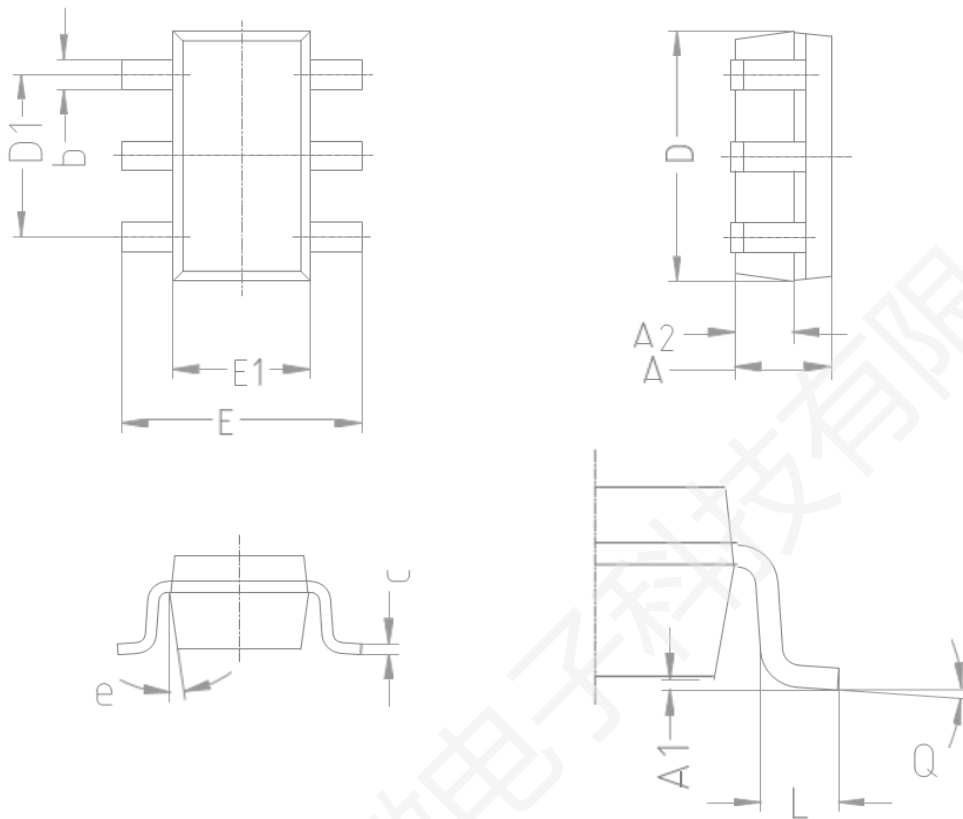


Figure 13: Max. Transient Thermal Impedance


$$Z_{thJA} = f(t_p); \text{ parameter: } D$$

Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


COMMON DIMENSION (MM)			
PKG	SOT23-6L		
Symbol	MIN	NOM	MAX
A	1.050	1.100	1.150
A1	0.010	0.060	0.150
A2	0.640	0.670	0.700
b	0.300	0.350	0.400
c	0.125	0.150	0.175
D	2.870	2.925	2.980
D1	1.800	1.900	2.000
E	2.650	2.800	2.950
E1	1.550	1.610	1.670
L	0.300	0.450	0.600
e	8°		
Q	0°	4°	8°

Revision History:

Revison	Date	Descriptions
Rev 1.1	July.2025	Initial Version

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